

Thomas Seyller

List of Publications by Year in descending order

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194
papers

21,934
citations

20817

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146
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199
docs citations

199
times ranked

20397
citing authors

#	ARTICLE	IF	CITATIONS
1	Pump-induced terahertz anisotropy in bilayer graphene. <i>Physical Review B</i> , 2022, 105, .	3.2	2
2	Hardness Enhancement in CoCrFeNi $_{1-x}$ (WC) $_x$ High-Entropy Alloy Thin Films Synthesised by Magnetron Co-Sputtering. <i>Coatings</i> , 2022, 12, 269.	2.6	0
3	Stacking Relations and Substrate Interaction of Graphene on Copper Foil. <i>Advanced Materials Interfaces</i> , 2021, 8, 2002025.	3.7	4
4	Influence of Nanoarchitectures on Interlayer Interactions in Layered Bi $_{0.97}$ MoSe Heterostructures. <i>Journal of Physical Chemistry C</i> , 2021, 125, 9469-9478.	3.1	4
5	CoCrFeNi High-Entropy Alloy Thin Films Synthesised by Magnetron Sputter Deposition from Spark Plasma Sintered Targets. <i>Coatings</i> , 2021, 11, 468.	2.6	10
6	Challenging the Durability of Intermetallic Mo $_{0.97}$ Ni Compounds in the Hydrogen Evolution Reaction. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 23616-23626.	8.0	27
7	Anisotropic Terahertz Pump-Probe Response of Bilayer Graphene. , 2021, , .		0
8	Synthesis and Electrical Properties of a New Compound (Bi $_{0.97}$ (Bi $_2$ Se $_3$) $_{1.26}$ (BiSe) $_{0.97}$ (MoSe $_2$) $_4$) Containing Metallic 1T-MoSe $_2$. <i>Chemistry of Materials</i> , 2021, 33, 6403-6411.		7
9	Electronic band structure of Bi-intercalate layers in graphene and SiC(0001). <i>Journal of the Korean Physical Society</i> , 2021, 78, 157-163.	0.7	2
10	Ultrafast electronic linewidth broadening in the C π core level of graphene. <i>Physical Review B</i> , 2021, 104, .	4.2	16
11	Surface Transport Properties of Pb-Intercalated Graphene. <i>Materials</i> , 2021, 14, 7706.	2.9	11
12	Silicon Carbide Stacking-Order-Induced Doping Variation in Epitaxial Graphene. <i>Advanced Functional Materials</i> , 2020, 30, 2004695.	14.9	17
13	Annealing effects on a-SiC:H and a-SiCN:H films deposited by plasma CVD methods. <i>Vacuum</i> , 2020, 178, 109410.	3.5	5
14	From a Cerium-Doped Polynuclear Bismuth Oxido Cluster to $\text{Bi}_2\text{O}_3\text{:Ce}$. <i>Inorganic Chemistry</i> , 2020, 59, 3353-3366.	4.0	14
15	Substrate induced nanoscale resistance variation in epitaxial graphene. <i>Nature Communications</i> , 2020, 11, 555.	12.8	19
16	Production and processing of graphene and related materials. <i>2D Materials</i> , 2020, 7, 022001.	4.4	333
17	Synthesis and Properties of (Bi $_{0.97}$ MoSe $_2$): A Heterostructure Containing Both 2H-MoSe $_2$ and 1T-MoSe $_2$. <i>Chemistry of Materials</i> , 2019, 31, 5824-5831.	6.7	14
18	Electronic structure of designed [(SnSe) $_1$ Te] $_m$ [TiSe $_2$] $_2$ heterostructure thin films with tunable layering sequence. <i>Journal of Materials Research</i> , 2019, 34, 1965-1975.	2.6	4

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19	Growth of Nanocrystalline MoSe ₂ Monolayers on Epitaxial Graphene from Amorphous Precursors (Phys. Status Solidi B 2/2019). Physica Status Solidi (B): Basic Research, 2019, 256, 1970015.	1.5	0
20	Surfaces, Interfaces, and Nanostructures: Spectroscopic Characterization and Applications. Physica Status Solidi (B): Basic Research, 2019, 256, 1900027.	1.5	0
21	Quasi-Freestanding Graphene on SiC(0001) by Ar-Mediated Intercalation of Antimony: A Route Toward Intercalation of High-Vapor-Pressure Elements. Annalen Der Physik, 2019, 531, 1900199.	2.4	17
22	Growth of Nanocrystalline MoSe ₂ Monolayers on Epitaxial Graphene from Amorphous Precursors. Physica Status Solidi (B): Basic Research, 2019, 256, 1800283.	1.5	1
23	Charge transfer in (PbSe) _{1+x} (NbSe) ₂ and (SnSe) _{1+x} (NbSe) ₂ heterocrystals investigated by photoelectron spectroscopy. Journal of Physics Condensed Matter, 2018, 30, 055001.	1.8	9
24	Extremely flat band in bilayer graphene. Science Advances, 2018, 4, eaau0059.	10.3	89
25	Direct observation of grain boundaries in graphene through vapor hydrofluoric acid (VHF) exposure. Science Advances, 2018, 4, eaar5170.	10.3	25
26	Work function of graphene multilayers on SiC(0001). 2D Materials, 2017, 4, 015043.	4.4	58
27	Growth and Intercalation of Graphene on Silicon Carbide Studied by Low-Energy Electron Microscopy. Annalen Der Physik, 2017, 529, 1700046.	2.4	17
28	Single Crystalline Metal Films as Substrates for Graphene Growth. Annalen Der Physik, 2017, 529, 1700023.	2.4	5
29	Science and Technology of Graphene. Annalen Der Physik, 2017, 529, 1700322.	2.4	0
30	Nickel enhanced graphene growth directly on dielectric substrates by molecular beam epitaxy. Journal of Applied Physics, 2016, 120, 045309.	2.5	7
31	Comeback of epitaxial graphene for electronics: large-area growth of bilayer-free graphene on SiC. 2D Materials, 2016, 3, 041002.	4.4	135
32	Rashba splitting of 100-meV in Au-intercalated graphene on SiC. Applied Physics Letters, 2016, 108, .	3.3	24
33	Structural Changes in 2D BiSe Bilayers as n Increases in (BiSe) _{1+x} (NbSe) ₂ ($n = 1-4$) Heterostructures. ACS Nano, 2016, 10, 9489-9499.	14.6	16
34	Manifestation of nonlocal electron-electron interaction in graphene. Physical Review B, 2016, 94, .	3.2	14
35	Terahertz ratchet effects in graphene with a lateral superlattice. Physical Review B, 2016, 93, .	3.2	77
36	Robust Phonon-Plasmon Coupling in Quasifreestanding Graphene on Silicon Carbide. Physical Review Letters, 2016, 116, 106802.	7.8	30

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37	Porous Ge@C materials via twin polymerization of germanium($\langle\text{sc}\rangle\text{ii}\langle\text{sc}\rangle$) salicyl alcoholates for Li-ion batteries. <i>Journal of Materials Chemistry A</i> , 2016, 4, 2705-2719.	10.3	21
38	Ramifications of optical pumping on the interpretation of time-resolved photoemission experiments on graphene. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2015, 200, 340-346.	1.7	26
39	Ultrafast electron dynamics in epitaxial graphene investigated with time- and angle-resolved photoemission spectroscopy. <i>Journal of Physics Condensed Matter</i> , 2015, 27, 164206.	1.8	37
40	Tunable Carrier Multiplication and Cooling in Graphene. <i>Nano Letters</i> , 2015, 15, 326-331.	9.1	80
41	Science and technology roadmap for graphene, related two-dimensional crystals, and hybrid systems. <i>Nanoscale</i> , 2015, 7, 4598-4810.	5.6	2,452
42	Polarization doping of graphene on silicon carbide. <i>2D Materials</i> , 2014, 1, 035003.	4.4	84
43	Healing of graphene on single crystalline Ni(111) films. <i>Applied Physics Letters</i> , 2014, 105, 191612.	3.3	16
44	Development and character of gap states on alkali doping of molecular films. <i>New Journal of Physics</i> , 2014, 16, 023011.	2.9	27
45	Backside Monitoring of Graphene on Silicon Carbide by Raman Spectroscopy. <i>Materials Science Forum</i> , 2014, 778-780, 1166-1169.	0.3	0
46	Buffer layer free graphene on SiC(0001) via interface oxidation in water vapor. <i>Carbon</i> , 2014, 70, 258-265.	10.3	42
47	A universal transfer route for graphene. <i>Nanoscale</i> , 2014, 6, 889-896.	5.6	58
48	Luminescence, Patterned Metallic Regions, and Photon-Mediated Electronic Changes in Single-Sided Fluorinated Graphene Sheets. <i>ACS Nano</i> , 2014, 8, 7801-7808.	14.6	28
49	Quasi-freestanding epitaxial graphene transistor with silicon nitride top gate. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 305103.	2.8	5
50	Surface-Induced Hybridization between Graphene and Titanium. <i>ACS Nano</i> , 2014, 8, 7704-7713.	14.6	38
51	Experimental analysis of the thermal annealing of hard a-C:H films. <i>Diamond and Related Materials</i> , 2014, 45, 43-57.	3.9	25
52	Ultrafast Dynamics of Massive Dirac Fermions in Bilayer Graphene. <i>Physical Review Letters</i> , 2014, 112, 257401.	7.8	96
53	The Hall coefficient: a tool for characterizing graphene field effect transistors. <i>2D Materials</i> , 2014, 1, 035004.	4.4	3
54	Direct growth of quasi-free-standing epitaxial graphene on nonpolar SiC surfaces. <i>Physical Review B</i> , 2013, 88, .	3.2	43

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55	Coexisting massive and massless Dirac fermions in symmetry-broken bilayer graphene. <i>Nature Materials</i> , 2013, 12, 887-892.	27.5	164
56	Spin-resolved photoemission and <i>ab initio</i> theory of graphene/SiC. <i>Physical Review B</i> , 2013, 88, .	3.2	11
57	Tuning the charge carriers in epitaxial graphene on SiC(0001) from electron to hole via molecular doping with C60F48. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	29
58	Observation of 4 nm Pitch Stripe Domains Formed by Exposing Graphene to Ambient Air. <i>ACS Nano</i> , 2013, 7, 10032-10037.	14.6	48
59	Epitaxial Growth and Electronic Properties of Large Hexagonal Graphene Domains on Cu(111) Thin Film. <i>Applied Physics Express</i> , 2013, 6, 075101.	2.4	83
60	Strong Plasmon Reflection at Nanometer-Size Gaps in Monolayer Graphene on SiC. <i>Nano Letters</i> , 2013, 13, 6210-6215.	9.1	121
61	On the Way to Grapheneâ€™ Pronounced Fluorescence of Polyhydrogenated Graphene. <i>Angewandte Chemie - International Edition</i> , 2013, 52, 754-757.	13.8	108
62	Looking behind the scenes: Raman spectroscopy of top-gated epitaxial graphene through the substrate. <i>New Journal of Physics</i> , 2013, 15, 113006.	2.9	24
63	Mono- and few-layer nanocrystalline graphene grown on Al2O3(0 0 0 1) by molecular beam epitaxy. <i>Carbon</i> , 2013, 56, 339-350.	10.3	54
64	Friction and atomic-layer-scale wear of graphitic lubricants on SiC(0001) in dry sliding. <i>Wear</i> , 2013, 300, 78-81.	3.1	42
65	Formation of high-quality quasi-free-standing bilayer graphene on SiC(0 0 0 1) by oxygen intercalation upon annealing in air. <i>Carbon</i> , 2013, 52, 83-89.	10.3	104
66	Localized States Influence Spin Transport in Epitaxial Graphene. <i>Physical Review Letters</i> , 2013, 110, 067209.	7.8	61
67	Robust Graphene Membranes in a Silicon Carbide Frame. <i>ACS Nano</i> , 2013, 7, 4441-4448.	14.6	15
68	Annealing-induced magnetic moments detected by spin precession measurements in epitaxial graphene on SiC. <i>Physical Review B</i> , 2013, 87, .	3.2	24
69	Growth and electronic structure of boron-doped graphene. <i>Physical Review B</i> , 2013, 87, .	3.2	113
70	Electronâ€™ phonon coupling in quasi-free-standing graphene. <i>Journal of Physics Condensed Matter</i> , 2013, 25, 094001.	1.8	25
71	Direct View of Hot Carrier Dynamics in Graphene. <i>Physical Review Letters</i> , 2013, 111, 027403.	7.8	308
72	Fabry-Perot enhanced Faraday rotation in graphene. <i>Optics Express</i> , 2013, 21, 24736.	3.4	47

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73	Small scale rotational disorder observed in epitaxial graphene on SiC(0001). New Journal of Physics, 2013, 15, 023019.	2.9	8
74	Structural investigation of nanocrystalline graphene grown on (6 \times 3 $\sqrt{3}$)R30 $^\circ$ -reconstructed SiC surfaces by molecular beam epitaxy. New Journal of Physics, 2013, 15, 123034.	2.9	16
75	Contribution of the buffer layer to the Raman spectrum of epitaxial graphene on SiC(0001). New Journal of Physics, 2013, 15, 043031.	2.9	93
76	Silicon Nitride as Top Gate Dielectric for Epitaxial Graphene. Materials Science Forum, 2013, 740-742, 149-152.	0.3	1
77	Detecting the local transport properties and the dimensionality of transport of epitaxial graphene by a multi-point probe approach. Applied Physics Letters, 2013, 102, 033110.	3.3	10
78	Visualizing Atomic-Scale Negative Differential Resistance in Bilayer Graphene. Physical Review Letters, 2013, 110, 036804.	7.8	23
79	Influence of structural properties on ballistic transport in nanoscale epitaxial graphene cross junctions. Nanotechnology, 2012, 23, 395203.	2.6	4
80	Origin of Doping in Quasi-Free-Standing Graphene on Silicon Carbide. Physical Review Letters, 2012, 108, 246104.	7.8	218
81	Gated Epitaxial Graphene Devices. Materials Science Forum, 2012, 717-720, 675-678.	0.3	0
82	Growth and electronic structure of nitrogen-doped graphene on Ni(111). Physical Review B, 2012, 86, .	3.2	77
83	Classical to quantum crossover of the cyclotron resonance in graphene: a study of the strength of intraband absorption. New Journal of Physics, 2012, 14, 095008.	2.9	24
84	Quantitative multichannel NC-AFM data analysis of graphene growth on SiC(0001). Beilstein Journal of Nanotechnology, 2012, 3, 179-185.	2.8	18
85	Implanted bottom gate for epitaxial graphene on silicon carbide. Journal Physics D: Applied Physics, 2012, 45, 154006.	2.8	6
86	Long Spin Relaxation Times in Wafer Scale Epitaxial Graphene on SiC(0001). Nano Letters, 2012, 12, 1498-1502.	9.1	121
87	Intrinsic Terahertz Plasmons and Magnetoplasmons in Large Scale Monolayer Graphene. Nano Letters, 2012, 12, 2470-2474.	9.1	224
88	Precise control of epitaxy of graphene by microfabricating SiC substrate. Applied Physics Letters, 2012, 101, 041605.	3.3	40
89	A momentum space view of the surface chemical bond. Physical Chemistry Chemical Physics, 2011, 13, 3604.	2.8	27
90	Multicomponent magneto-optical conductivity of multilayer graphene on SiC. Physical Review B, 2011, 84, .	3.2	44

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91	Terahertz Radiation Driven Chiral Edge Currents in Graphene. <i>Physical Review Letters</i> , 2011, 107, 276601.	7.8	118
92	Effective screening and the plasmaron bands in graphene. <i>Physical Review B</i> , 2011, 84, .	3.2	85
93	Highly p-doped epitaxial graphene obtained by fluorine intercalation. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	141
94	High-transconductance graphene solution-gated field effect transistors. <i>Applied Physics Letters</i> , 2011, 99, .	3.3	78
95	Epitaxial Graphene on SiC(0001). <i>Nanoscience and Technology</i> , 2011, , 135-159.	1.5	1
96	Bottom-gated epitaxial graphene. <i>Nature Materials</i> , 2011, 10, 357-360.	27.5	74
97	Giant Faraday rotation in single- and multilayer graphene. <i>Nature Physics</i> , 2011, 7, 48-51.	16.7	521
98	The interaction of Xe and Xe+K with graphene. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2011, 183, 118-124.	1.7	3
99	Transport properties of high-quality epitaxial graphene on 6H-SiC(0001). <i>Solid State Communications</i> , 2011, 151, 1061-1064.	1.9	20
100	The quasi-free-standing nature of graphene on H-saturated SiC(0001). <i>Applied Physics Letters</i> , 2011, 99, .	3.3	232
101	Strong phonon-plasmon coupled modes in the graphene/silicon carbide heterosystem. <i>Physical Review B</i> , 2010, 82, .	3.2	103
102	Influence of the growth conditions of epitaxial graphene on the film topography and the electron transport properties. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 687-690.	2.7	15
103	Automated preparation of high-quality epitaxial graphene on 6H-SiC(0001). <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 2924-2926.	1.5	62
104	HREELS study of graphene formed on hexagonal silicon carbide. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 394-397.	0.8	10
105	Atomic layer deposited aluminum oxide films on graphite and graphene studied by XPS and AFM. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 398-401.	0.8	41
106	Transport Properties of Single-Layer Epitaxial Graphene on 6H-SiC (0001). <i>Materials Science Forum</i> , 2010, 645-648, 637-641.	0.3	5
107	Quantum oscillations and quantum Hall effect in epitaxial graphene. <i>Physical Review B</i> , 2010, 81, .	3.2	168
108	Characteristics of solution gated field effect transistors on the basis of epitaxial graphene on silicon carbide. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 345303.	2.8	47

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109	The interaction of quasi-particles in graphene with chemical dopants. <i>New Journal of Physics</i> , 2010, 12, 125014.	2.9	10
110	Extended van Hove Singularity and Superconducting Instability in Doped Graphene. <i>Physical Review Letters</i> , 2010, 104, 136803.	7.8	294
111	Observation of Plasmarons in Quasi-Freestanding Doped Graphene. <i>Science</i> , 2010, 328, 999-1002.	12.6	375
112	Epitaxial Graphenes on Silicon Carbide. <i>MRS Bulletin</i> , 2010, 35, 296-305.	3.5	180
113	Friction and Dissipation in Epitaxial Graphene Films. <i>Physical Review Letters</i> , 2009, 102, 086102.	7.8	482
114	Low-temperature ballistic transport in nanoscale epitaxial graphene cross junctions. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	27
115	Photoemission of Ga _x Mn _x As with high Curie temperature and transformation into MnAs of zincblende structure. <i>Physica Status Solidi (B): Basic Research</i> , 2009, 246, 1435-1439.	1.5	7
116	Towards wafer-size graphene layers by atmospheric pressure graphitization of silicon carbide. <i>Nature Materials</i> , 2009, 8, 203-207.	27.5	2,396
117	The electronic structure of pentacene revisited. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2009, 174, 22-27.	1.7	20
118	Experimental studies of the electronic structure of graphene. <i>Progress in Surface Science</i> , 2009, 84, 380-413.	8.3	75
119	Quasiparticle Transformation during a Metal-Insulator Transition in Graphene. <i>Physical Review Letters</i> , 2009, 103, 056404.	7.8	208
120	Reconstruction of Molecular Orbital Densities from Photoemission Data. <i>Science</i> , 2009, 326, 702-706.	12.6	282
121	Raman Topography and Strain Uniformity of Large-Area Epitaxial Graphene. <i>Nano Letters</i> , 2009, 9, 964-968.	9.1	146
122	Alternative techniques to reduce interface traps in n-type 4H-SiC MOS capacitors. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1378-1389.	1.5	64
123	Effect of an intermediate graphite layer on the electronic properties of metal/SiC contacts. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1369-1377.	1.5	32
124	Epitaxial graphene: a new material. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1436-1446.	1.5	173
125	Molecular and electronic structure of PTCDA on bilayer graphene on SiC(0001) studied with scanning tunneling microscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 2064-2067.	1.5	54
126	Interaction, growth, and ordering of epitaxial graphene on SiC{0001} surfaces: A comparative photoelectron spectroscopy study. <i>Physical Review B</i> , 2008, 77, .	3.2	836

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127	Plasmon dispersion and damping in electrically isolated two-dimensional charge sheets. Physical Review B, 2008, 78, .	3.2	211
128	Origin of the energy bandgap in epitaxial graphene. Nature Materials, 2008, 7, 258-259.	27.5	170
129	Atomic and electronic structure of few-layer graphene on SiC(0001) studied with scanning tunneling microscopy and spectroscopy. Physical Review B, 2008, 77, .	3.2	340
130	Local work function measurements of epitaxial graphene. Applied Physics Letters, 2008, 93, .	3.3	211
131	Raman spectra of epitaxial graphene on SiC(0001). Applied Physics Letters, 2008, 92, .	3.3	305
132	Morphology of graphene thin film growth on SiC(0001). New Journal of Physics, 2008, 10, 023034.	2.9	156
133	Interface-induced complex electronic interference structures in Ag films on Ge(111). Physical Review B, 2008, 78, .	3.2	16
134	Morphology and electronic properties of metal organic molecular beam epitaxy grown ZnO on hydrogen passivated 6H-SiC(0001). Journal of Applied Physics, 2008, 103, 103720.	2.5	10
135	Photoemission Studies of Graphene on SiC: Growth, Interface, and Electronic Structure. , 2008, , 159-170.		24
136	Quantum size effects in quasi-free-standing Pb layers. Physical Review B, 2007, 75, .	3.2	45
137	Electronic Structure of Graphite/6H-SiC Interfaces. Materials Science Forum, 2007, 556-557, 701-704.	0.3	15
138	Initial Stages of the Graphite-SiC(0001) Interface Formation Studied by Photoelectron Spectroscopy. Materials Science Forum, 2007, 556-557, 525-528.	0.3	55
139	4H-SiC Metal-Oxide-Semiconductor (MOS) Capacitors Fabricated by Oxidation in a Tungsten Lamp Furnace in Combination with a Microwave Plasma and Subsequent Deposition of Al ₂ O ₃ . Materials Science Forum, 2007, 556-557, 627-630.	0.3	2
140	Symmetry breaking in few layer graphene films. New Journal of Physics, 2007, 9, 385-385.	2.9	174
141	Thermal stability of surface and interface structure of atomic layer deposited Al ₂ O ₃ on H-terminated silicon. Journal of Applied Physics, 2007, 102, 094503.	2.5	17
142	Interlayer Interaction and Electronic Screening in Multilayer Graphene Investigated with Angle-Resolved Photoemission Spectroscopy. Physical Review Letters, 2007, 98, 206802.	7.8	678
143	Renormalization of graphene bands by many-body interactions. Solid State Communications, 2007, 143, 63-71.	1.9	67
144	Quasiparticle dynamics in graphene. Nature Physics, 2007, 3, 36-40.	16.7	1,035

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145	Band structure and many body effects in graphene. European Physical Journal: Special Topics, 2007, 148, 5-13.	2.6	32
146	Interface of atomic layer deposited Al ₂ O ₃ on H-terminated silicon. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2194-2199.	1.8	12
147	How the solid state matrix affects the chemical shift of core-level binding energies: A novel method to take the induction effect into account. Solid State Communications, 2006, 139, 370-375.	1.9	3
148	Electronic properties of clean unreconstructed 6H-SiC(0001) surfaces studied by angle resolved photoelectron spectroscopy. Surface Science, 2006, 600, 3845-3850.	1.9	13
149	Structural and electronic properties of graphite layers grown on SiC(0001). Surface Science, 2006, 600, 3906-3911.	1.9	178
150	Controlling the Electronic Structure of Bilayer Graphene. Science, 2006, 313, 951-954.	12.6	3,003
151	Electronic properties of SiC surfaces and interfaces: some fundamental and technological aspects. Applied Physics A: Materials Science and Processing, 2006, 85, 371-385.	2.3	56
152	Publisher's Note: Correlation effects at ideal SiC{0001} (1 $\bar{1}$ -1) surfaces [Phys. Rev. B 73, 075412 (2006)]. Physical Review B, 2006, 73, .	3.2	1
153	Schottky barrier between 6H-SiC and graphite: Implications for metal/SiC contact formation. Applied Physics Letters, 2006, 88, 242103.	3.3	96
154	Correlation effects at ideal SiC{0001} (1 $\bar{1}$ -1) surfaces. Physical Review B, 2006, 73, .	3.2	22
155	Mapping disorder-induced changes to the Fermi surface of Cu ₃ Au using a new toroidal electron energy analyser. Journal of Electron Spectroscopy and Related Phenomena, 2005, 144-147, 515-518.	1.7	1
156	First results from a second generation toroidal electron spectrometer. Journal of Electron Spectroscopy and Related Phenomena, 2005, 144-147, 1001-1004.	1.7	59
157	ALD Deposited Al ₂ O ₃ Films on 6H-SiC(0001) after Annealing in Hydrogen Atmosphere. Materials Science Forum, 2005, 483-485, 559-562.	0.3	2
158	Hydrogen-Saturated SiC-Surfaces: Model Systems for Studies of Passivation, Reconstruction and Interface Formation. Materials Science Forum, 2005, 483-485, 535-540.	0.3	2
159	Surface Band Structure Studies of Si Rich Reconstructions on 4H-SiC(1-100). Materials Science Forum, 2005, 483-485, 547-550.	0.3	4
160	Hydrogen terminated 4H-SiC(11 $\bar{0}$ 0) and (112 $\bar{0}$) surfaces studied by synchrotron x-ray photoelectron spectroscopy. Physical Review B, 2005, 71, .	3.2	33
161	Initial Stages of Thermal Oxidation of 4H-SiC (11-20) Studied by Photoelectron Spectroscopy. Materials Science Forum, 2004, 457-460, 1317-1320.	0.3	7
162	The Atomic Structure of the Hydrogen Saturated a-Planes of 4H-SiC. Materials Science Forum, 2004, 457-460, 395-398.	0.3	5

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163	Passivation of hexagonal SiC surfaces by hydrogen termination. Journal of Physics Condensed Matter, 2004, 16, S1755-S1782.	1.8	87
164	Structural and Electronic Properties of the 6H-SiC(0001)/Al ₂ O ₃ Interface Prepared by Atomic Layer Deposition. Materials Science Forum, 2004, 457-460, 1369-1372.	0.3	3
165	The adsorption sites of rare gases on metallic surfaces: a review. Journal of Physics Condensed Matter, 2004, 16, S2839-S2862.	1.8	67
166	Stacking rearrangement at 6H-SiC(0001) surfaces during thermal hydrogenation. Surface Science, 2003, 532-535, 698-704.	1.9	7
167	Adsorption geometry of Cu(111)-(12 $\sqrt{3}$ × 2)-14Xe. Surface Science, 2003, 539, 165-170.	1.9	18
168	Doping of single-walled carbon nanotube bundles by Brønsted acids. Physical Chemistry Chemical Physics, 2003, 5, 5472-5476.	2.8	192
169	Al ₂ O ₃ prepared by atomic layer deposition as gate dielectric on 6H-SiC(0001). Applied Physics Letters, 2003, 83, 1830-1832.	3.3	98
170	Synchrotron x-ray photoelectron spectroscopy study of hydrogen-terminated 6H-SiC{0001} surfaces. Physical Review B, 2003, 67, .	3.2	48
171	Origin of the split Si-H stretch mode on hydrogen terminated 6H-SiC(0001): Titration of crystal truncation. Applied Physics Letters, 2002, 80, 4726-4728.	3.3	23
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